

1. General description

Maximum Efficiency General Application (MEGA) Schottky barrier rectifier, encapsulated in a CFP15 (SOT1289) power and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

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- Average forward current: $I_{F(AV)} \le 8 A$
- Reverse voltage: V_R ≤ 100 V
- Low leakage current due to high Schottky barrier technology
- Low forward voltage
- High power capability due to clip-bonding technology and heat sink
- High temperature $T_j \le 175 \degree C$
- Small and thin SMD power plastic package, typical height 0.78 mm
- AEC-Q101 qualified

3. Applications

- Low voltage rectification
- Automotive LED lighting
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption application

4. Quick reference data

Table 1. Qu	ick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; T _{amb} ≤ 155 °C; square wave	-	-	8	A
V _R	reverse voltage	T _j = 25 °C	-	-	100	V
V _F	forward voltage	$I_F = 8 \text{ A}; t_p \le 300 \text{ μs}; \delta \le 0.02 ;$ $T_j = 25 \text{ °C}$	-	770	850	mV
I _R	reverse current	$V_R = 100 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.03;$ $T_j = 25 \text{ °C}$	-	0.14	1	μA





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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	А	anode		
2	А	anode		
3	К	cathode	(2) CFP15 (SOT1289)	

6. Ordering information

Table 3. Ordering information							
Type number Package							
	Name	Description	Version				
PMEG100V080ELPD	CFP15	plastic, thermal enhanced ultra thin SMD package; 3 leads; body: 5.8 x 4.3 x 0.78 mm	SOT1289				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG100V080ELPD	100V L08E

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Limiting values 8.

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _R	reverse voltage	T _j = 25 °C		-	100	V
I _F	forward current	T _{sp} ≤ 150 °C; δ = 1		-	11.2	А
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; T _{amb} ≤ 155 °C; square wave		-	8	A
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	160	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.66	W
			[2]	-	2.15	W
			[3]	-	3.75	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint. [3]

Thermal characteristics 9.

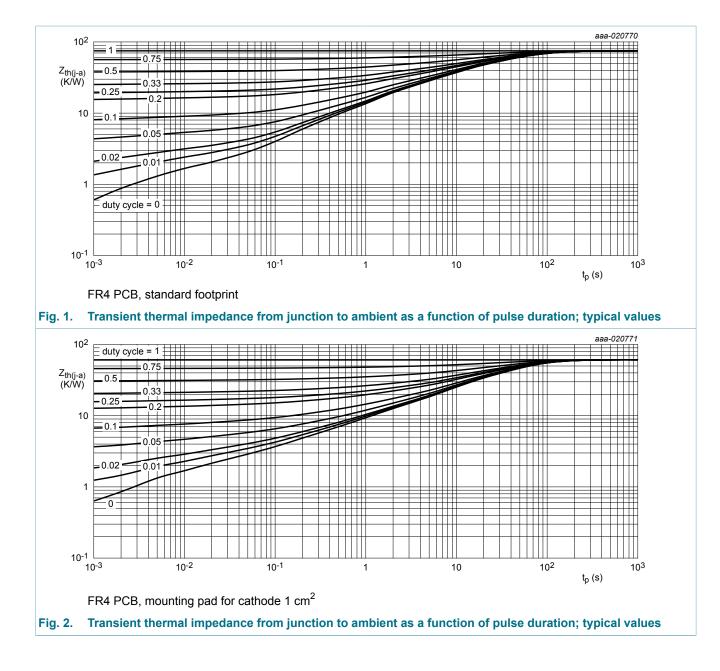
Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-α)	thermal resistance from junction to ambient	in free air	[1][2]	-	-	90	K/W
			[1][3]	-	-	70	K/W
			[1][4]	-	-	40	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	3	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. [2]
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.
- [5] Soldering point of cathode tab.

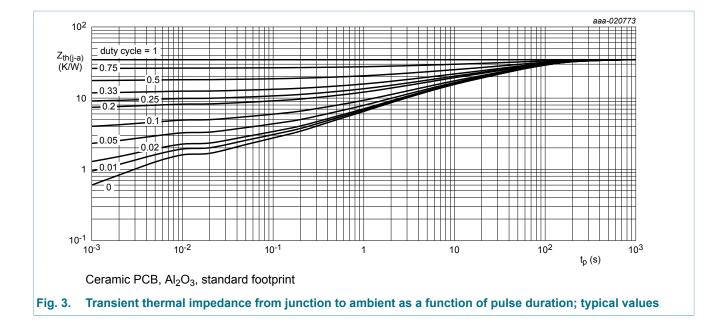
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{(BR)R}	reverse breakdown voltage	I_R = 1 mA; t _p ≤ 1.2 ms; δ ≤ 0.12; T _j = 25 °C; pulsed	100	-	-	V
V _F forward voltage	forward voltage	I_F = 0.1 A; t _p ≤ 300 μs; δ ≤ 0.02 ; T _j = 25 °C	-	440	-	mV
		I_F = 1 A; t _p ≤ 300 μs; δ ≤ 0.02 ; T _j = 25 °C	-	565	-	mV
	I_F = 2 A; t _p ≤ 300 μs; δ ≤ 0.02 ; T _j = 25 °C	-	635	740	mV	
		I_F = 4 A; t _p ≤ 300 μs; δ ≤ 0.02 ; T _j = 25 °C	-	705	790	mV
		I_F = 5 A; t _p ≤ 300 μs; δ ≤ 0.02 ; T _j = 25 °C	-	725	-	mV
		$I_F = 6 \text{ A}; t_p \le 300 \text{ μs}; \delta \le 0.02 ;$ $T_j = 25 \text{ °C}$	-	740	-	mV
		I_F = 8 A; t _p ≤ 300 μs; δ ≤ 0.02 ; T _j = 25 °C	-	770	850	mV
	I_F = 8 A; t _p ≤ 300 μs; δ ≤ 0.02; T _j = -40 °C	-	870	970	mV	
		I _F = 4 A; t _p ≤ 300 μs; δ ≤ 0.02; T _i = 125 °C	-	570	-	mV

PMEG100V080ELPD

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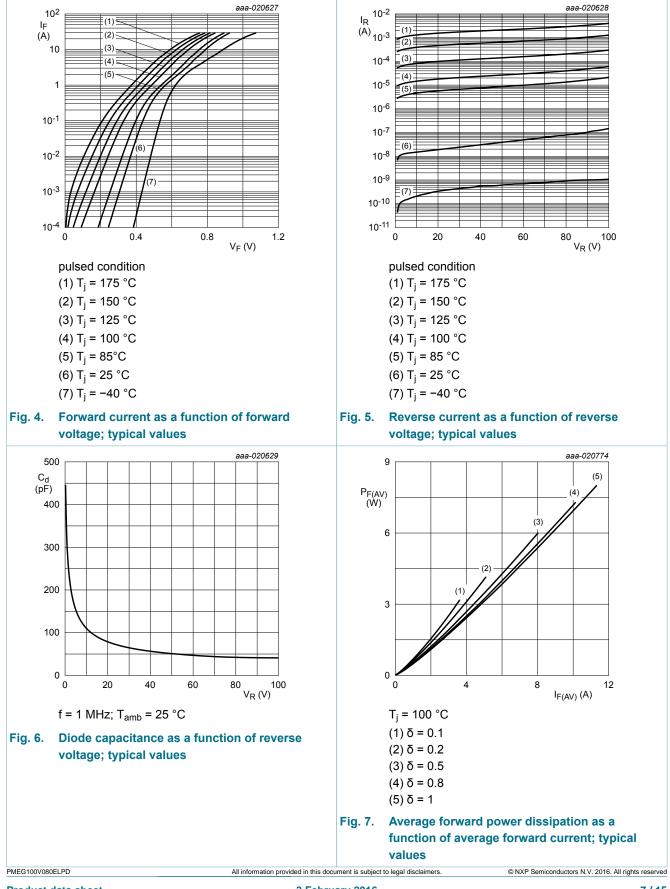
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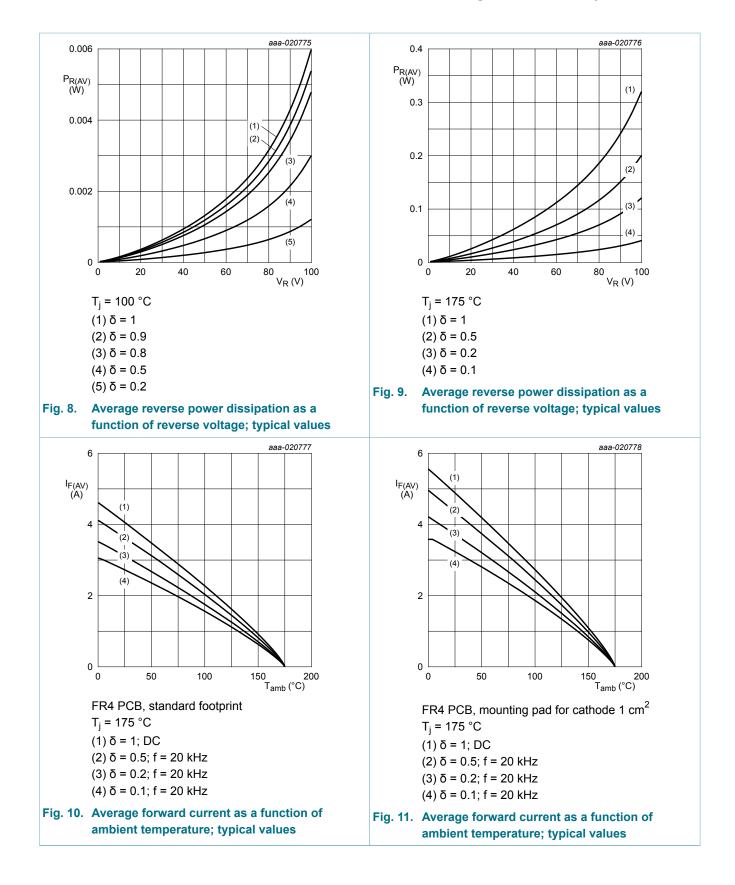
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I _F = 8 A; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 125 °C	-	635	740	mV
I _R	reverse current	$V_R = 60 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.03;$ $T_j = 25 \text{ °C}$	-	0.05	-	μA
		$V_R = 80 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.03;$ $T_j = 25 \text{ °C}$	-	0.075	-	μA
		V_R = 100 V; $t_p \le 3$ ms; $\delta \le 0.03$; T_j = 25 °C	-	0.14	1	μA
		V_R = 100 V; $t_p \le 3$ ms; $\delta \le 0.03$; T _j = 125 °C	-	0.3	1.5	mA
		$V_R = 60 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.03;$ $T_j = 150 \text{ °C}$	-	0.72	2	mA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	275	-	pF
		V _R = 4 V; f = 1 MHz; T _j = 25 °C	-	170	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	110	-	pF
t _{rr}	reverse recovery time	$I_{\rm F}$ = 0.5 A; $I_{\rm R}$ = 0.5 A; $I_{\rm R(meas)}$ = 0.1 A; $T_{\rm j}$ = 25 °C	-	10	-	ns
V _{FRM}	peak forward recovery voltage	$I_F = 0.5 \text{ A}; \text{ d}I_F/\text{d}t = 20 \text{ A}/\mu\text{s}; T_j = 25 ^\circ\text{C}$	-	535	-	mV

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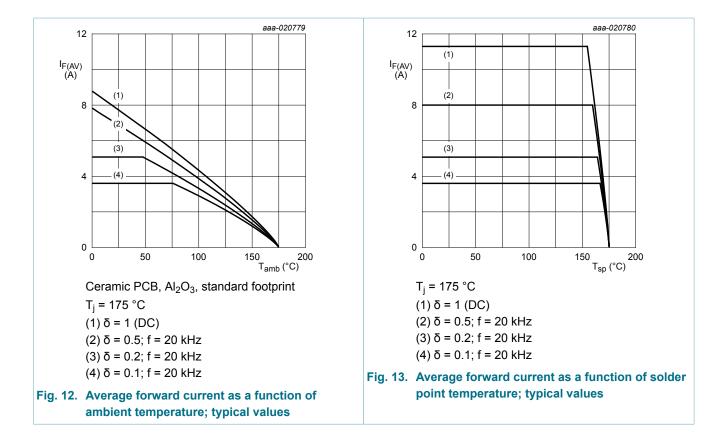
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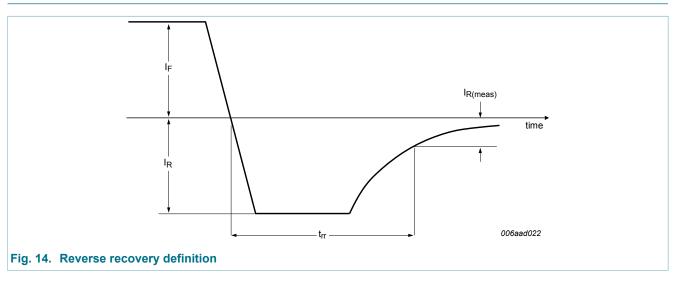
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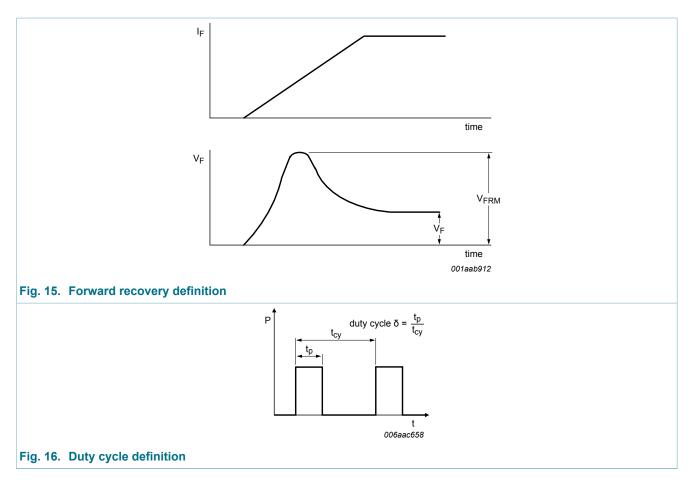


11. Test information



PMEG100V080ELPD

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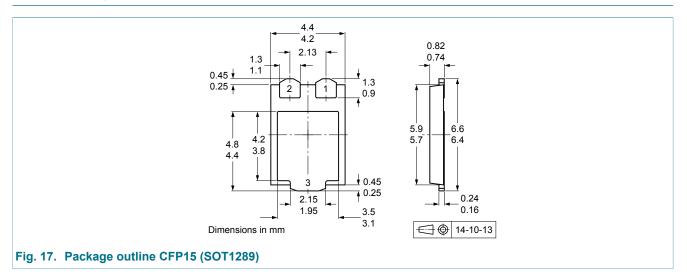
The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

11.1 Quality information

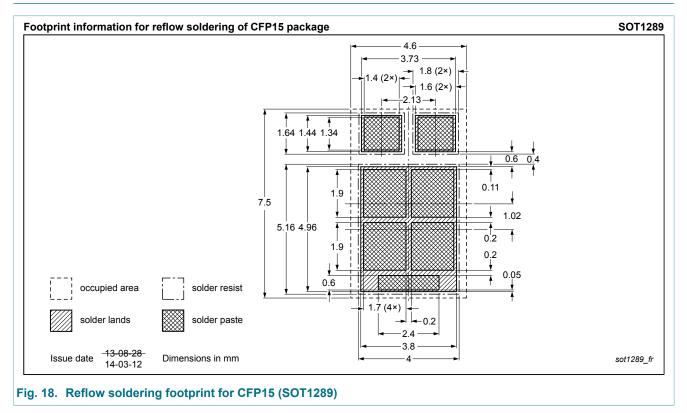
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMEG100V080ELPD v.2	20160203	Product data sheet	-	PMEG100V080ELPD v.1			
Modifications:	Added Figures 1 to	3 and 7 to 13					
PMEG100V080ELPD v.1	20151117	Preliminary data sheet	-	-			

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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	Features and benefits

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